

Abstract Submitted
for the CUWIP22 Meeting of
The American Physical Society

Phase Diagram of Valence Transition below 14T and above 2K for $\text{Ce}_{1-x}\text{Pr}_x\text{Os}_4\text{Sb}_{12}$, $x=0.1$ and 0.2 ¹ LETICIA RAMOS, XINGYU ZHAO, ZACHARY CARRENDER, California State University, Fresno, TATSUYA YANAGISAWA, Hokkaido University, Sapporo, M. BRIAN MAPLE, University of California, San Diego, PEI-CHUN HO, California State University, Fresno — Filled skutterudite compounds are described by the chemical formula: $\text{LnT}_4\text{Pn}_{12}$ where Ln is a rare-earth metal, T is a transition metal, and Pn is a pnictogen. $\text{CeOs}_4\text{Sb}_{12}$ is a Kondo insulator that exhibits antiferromagnetism due to spin-density wave formation below 1 K. Based on the band-structure calculation, $\text{CeOs}_4\text{Sb}_{12}$ is suggested to be a candidate for topological insulators, which may have a hole Fermi surface and an electron Fermi surface coexisting at low temperatures. Through our previous studies of $\text{CeOs}_4\text{Sb}_{12}$, we found that a valence transition occurs in this compound, and we have established an intriguing temperature, T -, magnetic field, H , phase diagram in its normal state. Nevertheless, the neighboring isostructural compound $\text{PrOs}_4\text{Sb}_{12}$ is a heavy-fermion superconductor with a transition temperature at 1.85 K. When Pr substitutes Ce in $\text{CeOs}_4\text{Sb}_{12}$, a hole-doping is introduced. We plan to study the series of $\text{Ce}_{1-x}\text{Pr}_x\text{Os}_4\text{Sb}_{12}$ to investigate the influence of hole-doping to the valence transition. In this report, we will show the preliminary results of normal state resistivity of two concentrations: $x=0.1$ and $x=0.2$ from 300 K to 2 K in magnetic fields ranging from 0 to 14 Tesla as well as the $T - H$ phase diagram updated with the doped samples' resistance data.

¹CSU-Fresno is supported by NSF DMR-1905636; at UCSD by US DOE DE-FG02-04ER46105 and NSF DMR-1810310; and at Hokkaido U. by JSPS KAKENHI JP 21KK0046.

Leticia Ramos
California State University, Fresno

Date submitted: 06 Jan 2022

Electronic form version 1.4